

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5465

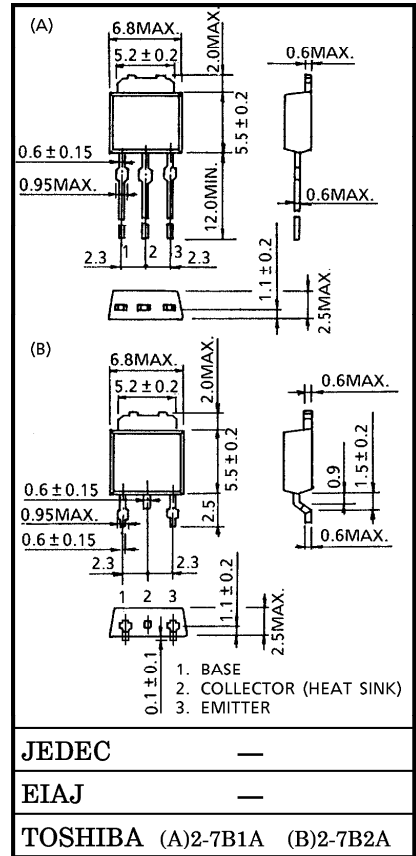
SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS

HIGH SPEED DC-DC CONVERTER APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- Excellent Switching Times ($I_C = 0.08\text{ A}$)
: $t_r = 0.7\ \mu\text{s}$ (Max.), $t_f = 0.5\ \mu\text{s}$ (Max.)
- High Collector Breakdown Voltage : $V_{CEO} = 800\text{ V}$



MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	900	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current	DC	I_C	0.8
	Pulse	I_{CP}	1.5
Base Current	I_B	0.2	A
Collector Power Dissipation	$T_a = 25^\circ\text{C}$	P_C	1.0
	$T_c = 25^\circ\text{C}$		20
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

JEDEC	—
EIAJ	—
TOSHIBA	(A)2-7B1A (B)2-7B2A

Weight : 0.36 g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 800\text{ V}, I_E = 0$	—	—	100	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	1	mA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	$I_C = 1\text{ mA}, I_E = 0$	900	—	—	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	800	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$	10	—	—	
		$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 0.08\text{ A}$	15	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 0.3\text{ A}, I_B = 0.06\text{ A}$	—	—	1.0	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 0.3\text{ A}, I_B = 0.06\text{ A}$	—	—	1.3	V
Switching Time	Rise Time	t_r	<p> $20\ \mu\text{s}$ I_{B1} INPUT I_{B2} OUTPUT $1.3\text{ k}\Omega$ $V_{CC} = 400\text{ V}$ $I_{B1} = 0.06\text{ A}, I_{B2} = -0.12\text{ A}$ DUTY CYCLE $\leq 1\%$ </p>	—	—	0.7	μs
	Storage Time	t_{stg}		—	—	3.0	
	Fall Time	t_f		—	—	0.5	

